



《风光欣》技术资料

S 9012

PNP EPITAXIAL SILICON TRANSISTOR

1W OUTPUT AMPLIFIER OF PORTABLE RADIOS IN CLASS

B PUSH-PULL OPERATION

*High Collector Current($I_{cm} = -500mA$)

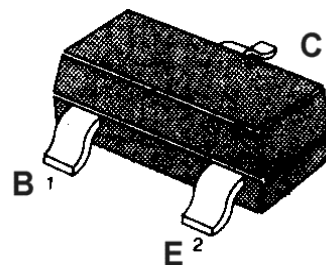
*Complementary to **S9013**

*Excelent hFE linearity.

ABSOLUTE MAXIMUM RATINGS($T_a=25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter -Base Voltage	V_{EBO}	-5	V
Collector Current	I_c	-500	mA
Collector Dissipation	P_c	225	mW
Junction Temperature	T_j	150	
Storage Temperature	T_{STG}	-55 ~150	

SOT-23



ELECTRICAL CHARACTERISTICS($T_a=25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c = -100 \mu A, I_E = 0$	-40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c = -1mA, I_B = 0$	-20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -100 \mu A, I_c = 0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -25V, I_E = 0$			-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -3V, I_c = 0$			-100	nA
DC Current Gain	Hfe	$V_{CE} = -1V, I_c = -50mA$	64	120	300	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = -500mA, I_B = -50mA$		-0.18	-0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = -500mA, I_B = -50mA$		-0.95	-1.2	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = -1V, I_c = -10mA$	-0.6	-0.67	-0.7	V

Hfe CLASSIFICATION

Classification	L	H
$H_{FE(1)}$	120-200	200-350